



DONGGUAN NANJING ELECTRONICS LTD.,

TO-92 Plastic-Encapsulate Transistors

A94 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.625 W (Tamb=25°C)

Collector current

I_{CM} : -0.2 A

Collector-base voltage

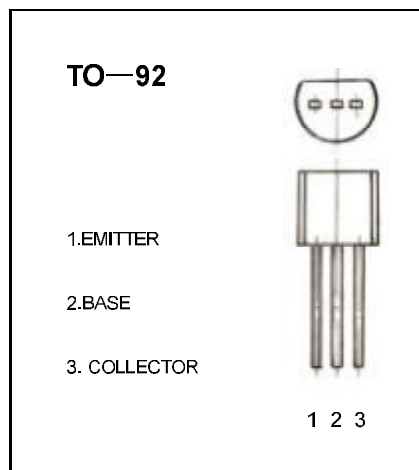
$V_{(BR)CBO}$: -400 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

ELECTRICAL CHARACTERISTICS (Tamb=25 °C

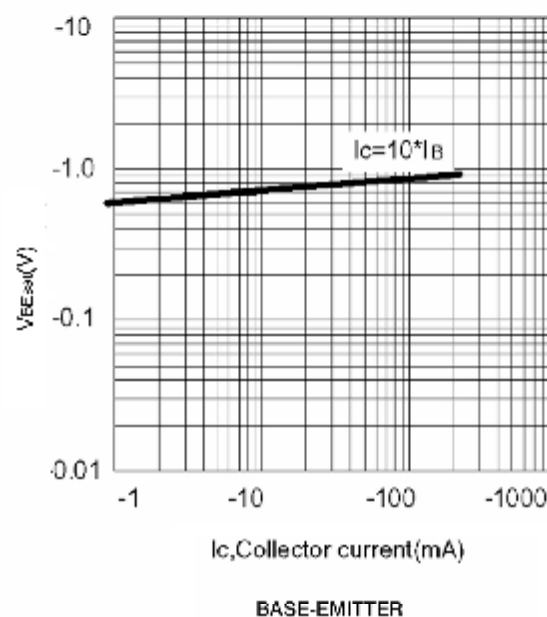
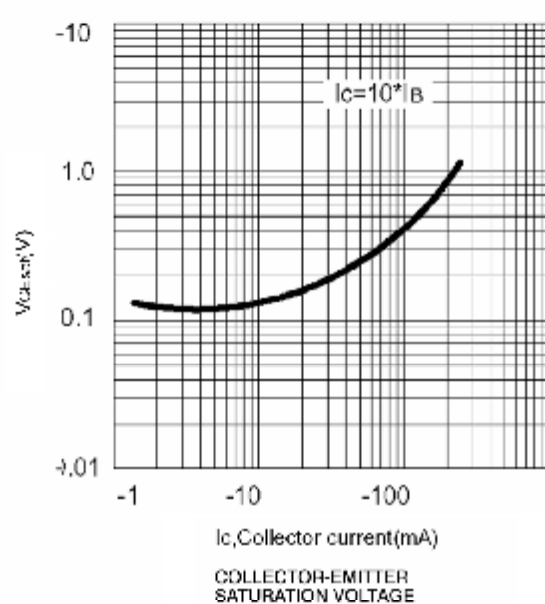
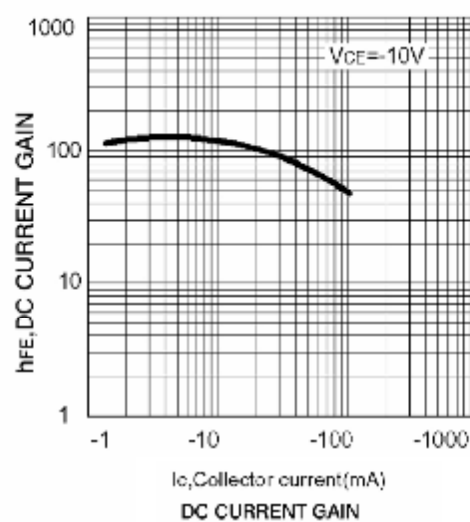
unless otherwise specified)



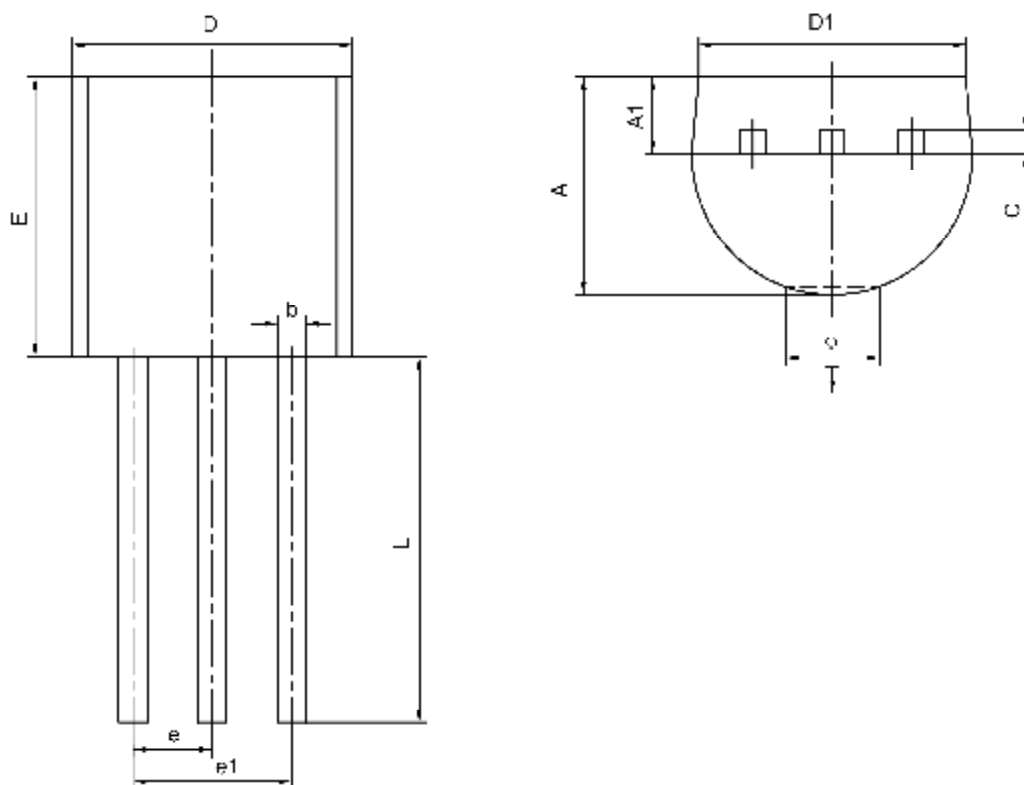
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -400 V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -400 V, I_B = 0$			-5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -10 mA$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	70			
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -100 mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 mA, I_B = -1mA$			-0.2	V
	$V_{CE(sat)}$	$I_C = 50 mA, I_B = -5mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10 mA, I_B = -1 mA$			-0.75	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA, f = 30MHz$	50			MHz

Typical Characteristics

A94



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ø		1.600		0.063
T	0.000	0.380	0.000	0.015